

# Features

- High isolation 5000 VRMS
- Patented coplanar structure DMC-Isolator®
- Various CTR selection available
- DC input with transistor output
- Low current operation guaranteed
- Operating Temperature range 55 °C to 110 °C
- External Creepage ≥ 7.0mm
- Distance Through Isolation ≥ 0.4mm
- Clearances Distance  $\geq$  7.5mm (S/SL Type)
- Clearances Distance ≥ 8.0mm (M/SLM Type)
- RoHS and REACH compliance
- Halogen Free compliance (Optional)
- MSL class 1
- Regulatory Approvals
  - ✓ UL UL1577 (E364000)
  - ✓ VDE EN60747-5-5(VDE0884-5)
  - ✓ CQC GB4943.1, GB8898 (14001104781)
  - ✓ IEC62368 (FI/41119)

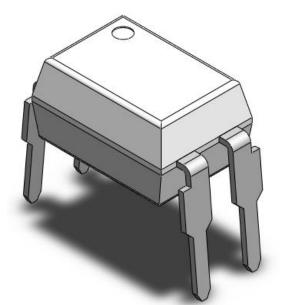
### Description

The CT816D3 series consists of a photo transistor optically coupled to an Infrared-emitting diode in a 4-lead DIP DMC-Isolator<sup>®</sup> package with different lead forming options.

## Applications

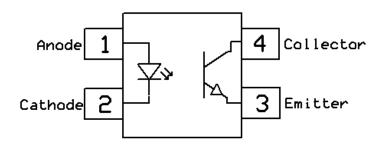
- Switch mode power supplies
- Computer peripheral interface
- Microprocessor system interface

## Package Outline



Note: Different bending options available. See package dimension

## Schematic





### Absolute Maximum Ratings $T_A = 25^{\circ}C$ , unless otherwise specified

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

| Symbol            | Parameters                                      | Ratings    | Units | Notes |
|-------------------|---|------------|-------|-------|
| Viso              | Isolation voltage (AC, 1 minute, 40 ~ 60% R.H.) | 5000       | VRMS  |       |
| Ρτοτ              | Total power dissipation                         | 200        | mW    |       |
| TOPR              | Operating temperature                           | -55 ~ +110 | °C    |       |
| Tstg              | Storage temperature                             | -55 ~ +150 | °C    |       |
| Tsol              | Soldering temperature (For 10 seconds)          | 260        | °C    |       |
| Emitter           |   | <b>-</b>   |       | •     |
| l <sub>F</sub>    | Forward current                                 | 60         | mA    |       |
| F(TRANS)          | Peak transient current (≤1µs P.W,300pps)        | 1          | А     |       |
| VR                | Reverse voltage                                 | 6          | V     |       |
| PD                | Emitter power dissipation                       | 100        | mW    |       |
| Detector          | ſ   |            | ·     |       |
| PD                | Detector power dissipation                      | 150        | mW    |       |
| B <sub>VCEO</sub> | Collector-Emitter Breakdown Voltage             | 80         | V     |       |
| BVECO             | Emitter-Collector Breakdown Voltage             | 6          | V     |       |
| lc                | Collector Current                               | 50         | mA    |       |



## **Electrical Characteristics** $T_A = 25^{\circ}C$ (unless otherwise specified)

#### **Emitter Characteristics**

| Symbol | Parameters        | Test Conditions | Min | Тур  | Max  | Units | Notes |
|--------|-------------------|-----------------|-----|------|------|-------|-------|
| VF     | Forward voltage   | IF=10mA         |     | 1.24 | <1.3 | V     |       |
| IR     | Reverse Current   | $V_R = 6V$      | -   | -    | 5    | μA    |       |
| CIN    | Input Capacitance | f= 1MHz         | -   | 30   | -    | pF    |       |

#### **Detector Characteristics**

| Symbol            | Parameters                     | Test Conditions                            | Min | Тур | Max | Units | Notes |
|-------------------|--------------------------------|--|-----|-----|-----|-------|-------|
| B <sub>VCEO</sub> | Collector-Emitter Breakdown    | Ic= 100μA                                  | 80  | -   | -   | V     |       |
| BVECO             | Emitter-Collector Breakdown    | I <sub>E</sub> = 100μA                     | 6   | -   | -   | V     |       |
| ICEO              | Collector-Emitter Dark Current | V <sub>CE</sub> = 20V, I <sub>F</sub> =0mA | -   | -   | 100 | nA    |       |

#### **Transfer Characteristics**

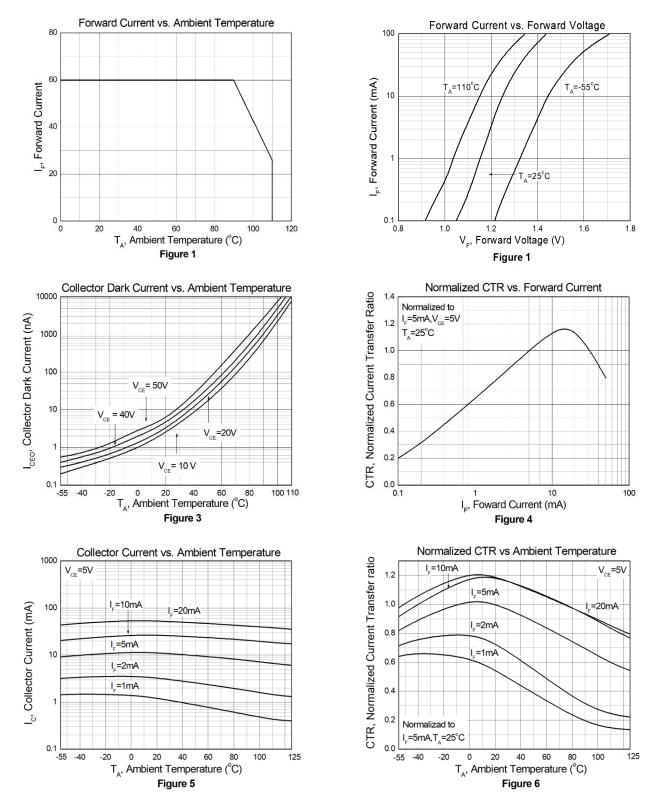
| Symbol               | Parameters                   | Test Conditions                                | Min                | Тур | Max | Units | Notes |
|----------------------|------------------------------|--|--------------------|-----|-----|-------|-------|
| CTR                  | Current Transfer Ratio       | I <sub>F</sub> = 0.1mA, V <sub>CE</sub> = 0.4V | 10                 | 30  | -   |       |       |
|                      |                              | IF= 2mA, VCE= 5V                               | 200                | -   | 500 | %     |       |
|                      |                              | IF= 5mA, V <sub>CE</sub> = 5V                  | 300                | -   | 450 |       |       |
| N                    | Collector-Emitter Saturation |  |                    | 0.1 | 0.0 | V     |       |
| V <sub>CE(SAT)</sub> | Voltage                      | I <sub>F</sub> = 20mA, I <sub>C</sub> = 1mA    | -                  | 0.1 | 0.2 | V     |       |
| Rio                  | Isolation Resistance         | VIO= 500VDC                                    | 5x10 <sup>10</sup> | -   | -   | Ω     |       |
| Сю                   | Isolation Capacitance        | f= 1MHz  | -                  | 0.5 | 1   | pF    |       |

#### **Switching Characteristics**

| Symbol         | Parameters | Test Conditions                                      | Min | Тур | Max | Units | Notes |
|----------------|------------|--|-----|-----|-----|-------|-------|
| tr             | Rise Time  | L 2m ( )/ 2)/ D 1000                                 | -   | 6   | 18  | 0     |       |
| t <sub>f</sub> | Fall Time  | Ic= 2mA, V <sub>CE</sub> = 2V, R <sub>L</sub> = 100Ω | -   | 8   | 18  | μs    |       |

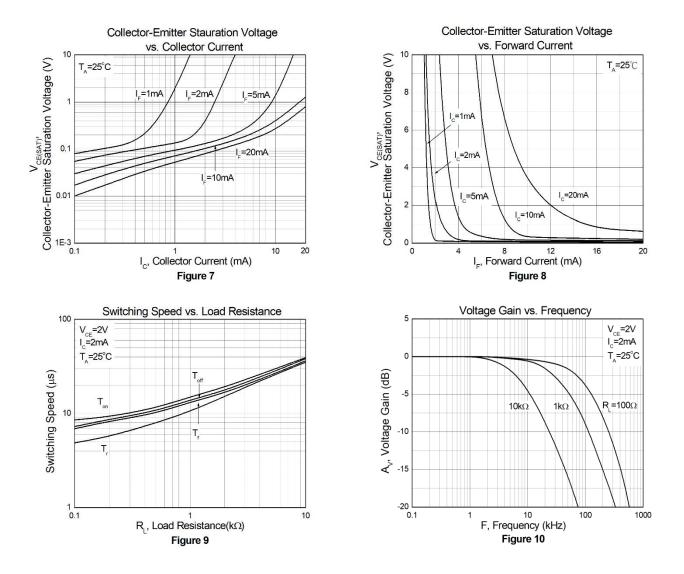


### **Typical Characteristic Curves** $T_A = 25^{\circ}C$ , unless otherwise specified





## Typical Characteristic Curves $T_A = 25^{\circ}C$ , unless otherwise specified (Continued)





## **Test Circuit**

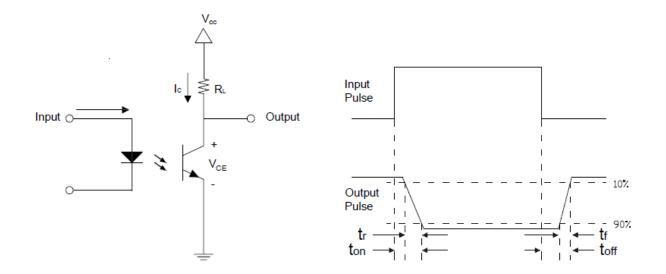
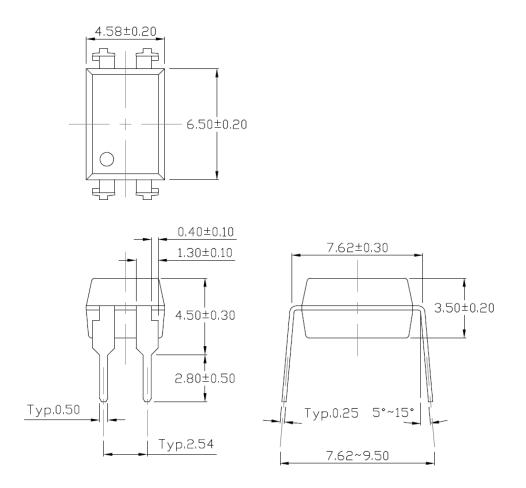


Figure 11: Switching Time Test Circuits

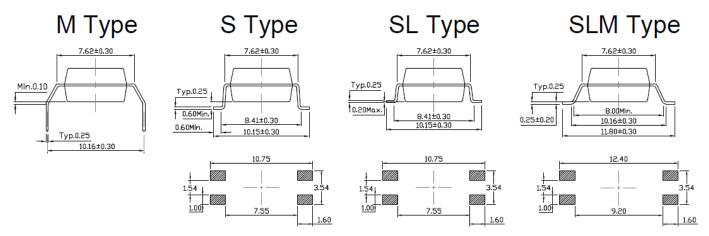


Package Dimension Dimensions in mm unless otherwise stated

### Standard DIP – Through Hole



### Forming Option Dimensions in mm unless otherwise stated





# CT816D3 Series

DC Input 4-Pin DMC-Isolator®

**Phototransistor Optocoupler** 

: VDE Safety Mark Option (Blank or V)

: Denotes "CT Micro"

: One Digit Year Code

: Two Digit Work Week

: Manufacturing Code

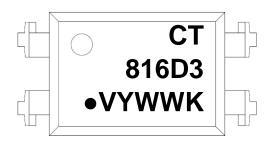
: Lead Frame Material Option

(Blank : Iron ; • : Copper)

: Part Number

: CTR Rank

## Marking Information



## **Ordering Information**

# CT816D4 (V)(Y)(Z)-HG

- CT = Denotes "CT Micro"
- 816 = Part Number
- D3 = CTR Rank
- V = VDE Safety Mark Option (Blank or V)
- Y = Lead Form Option (S, SL, M, SLM or Blank)
- Z = Tape and Reel Option (Blank, T1 or T2)
- H = Lead Frame Option (H: Iron, Blank: Copper)
- G = Material Option (G: Halogen Free, Blank: Non-Halogen Free)

| Option  | Description   | Quantity        |
|---------|---|-----------------|
| None    | Standard 4 Pin DIP  | 100 Units/Tube  |
| М       | Gullwing (400mil) Lead Forming                                  | 100 Units/Tube  |
| S(T1)   | Surface Mount Lead Forming – With Option 1 Taping               | 1500 Units/Reel |
| S(T2)   | Surface Mount Lead Forming – With Option 2 Taping               | 1500 Units/Reel |
| SL(T1)  | Surface Mount (Low Profile) Lead Forming– With Option 1 Taping  | 1500 Units/Reel |
| SL(T2)  | Surface Mount (Low Profile) Lead Forming – With Option 2 Taping | 1500 Units/Reel |
| SLM(T1) | Surface Mount (Gullwing) Lead Forming– With Option 1 Taping     | 1500 Units/Reel |
| SLM(T2) | Surface Mount (Gullwing) Lead Forming – With Option 2 Taping    | 1500 Units/Reel |

Note: CT

816

D3

V

Y

Κ

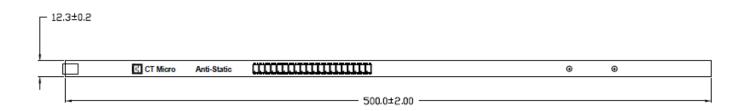
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WW

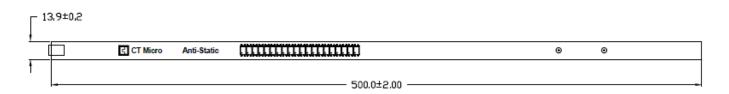


### Carrier Specifications Dimensions in mm unless otherwise stated

#### **Tube Option Standard DIP**



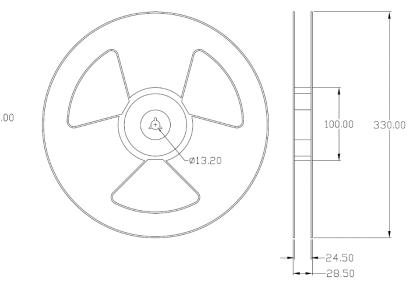
### Tube Option M Type



#### Reel Dimension All dimensions are in mm, unless otherwise stated

#### Option S(T1/T2) & SL(T1/T2)

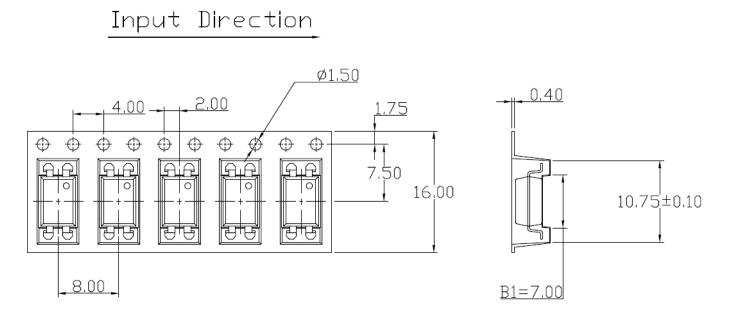
Option SLM(T1/T2)



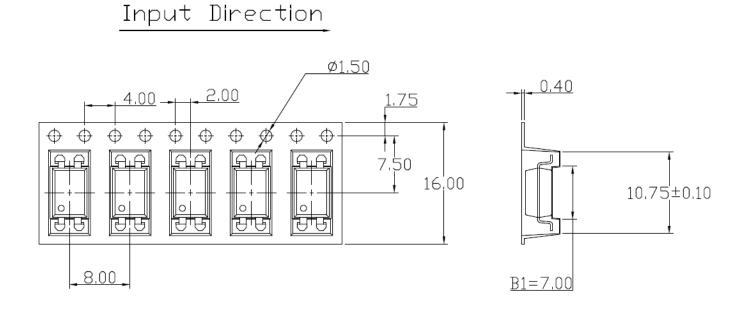


### Carrier Tape Specifications Dimensions in mm unless otherwise stated

## Option S(T1) & SL(T1)

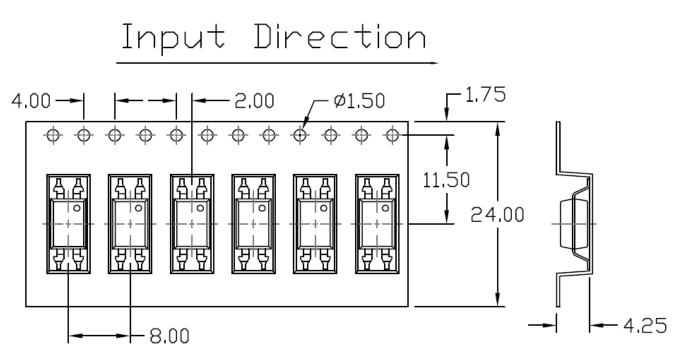


## Option S(T2) & SL(T2)

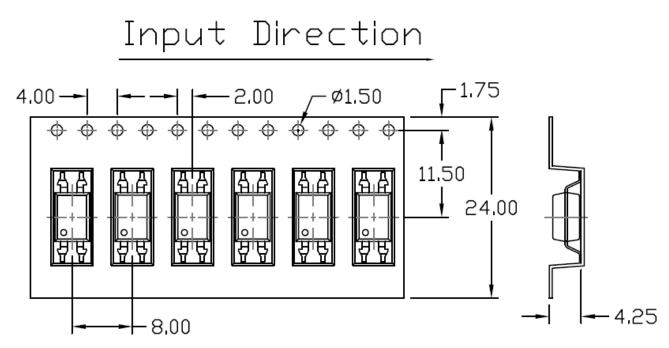




Option SLM(T1)



### **Option SLM(T2)**





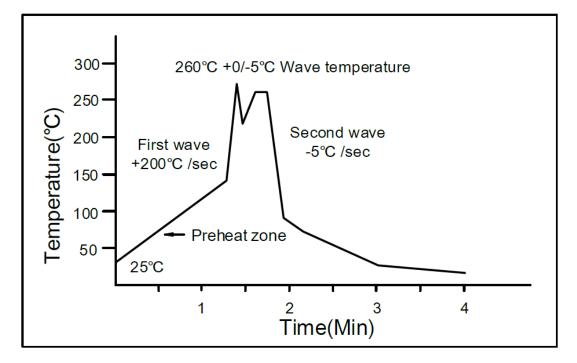
## Solderability spec (Follow the JEDEC standard JESD22-B102)

Reflow Soldering: Immersed surface, other than the end of pin as cut-surface, must be covered by solder.

Solder-Bath: More than 95% of the electrode must be covered with solder.

## Wave soldering (Follow the JEDEC standard JESD22-A111)

One time soldering is recommended within the condition of temperature. Temperature: 260+0/-5°C. Time: 10 sec. Preheat temperature: 25 to 140°C. Preheat time: 30 to 80 sec.

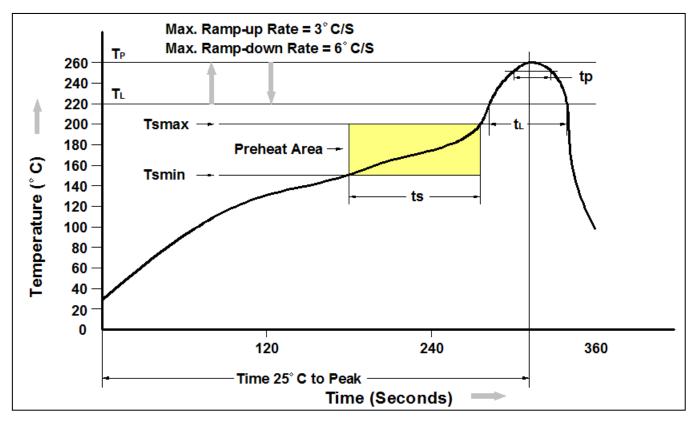


## Iron soldering (Follow the standard MIL-STD 202G, Method 210F)

Allow single lead soldering in every single process. One time soldering is recommended. Temperature: 350±10°C Time: 5 sec max.



## **Reflow Profile (Follow the JEDEC standard J-STD-020)**



| Profile Feature   | Pb-Free Assembly Profile |  |  |
|---|--------------------------|--|--|
| Temperature Min. (Tsmin)                                  | 150°C                    |  |  |
| Temperature Max. (Tsmax)                                  | 200°C                    |  |  |
| Time (ts) from (Tsmin to Tsmax)                           | 60-120 seconds           |  |  |
| Ramp-up Rate (t <sub>L</sub> to t <sub>P</sub> )          | 3°C/second max.          |  |  |
| Liquidous Temperature (TL)                                | 217°C                    |  |  |
| Time (t <sub>L</sub> ) Maintained Above (T <sub>L</sub> ) | 60 – 150 seconds         |  |  |
| Peak Body Package Temperature                             | 260°C +0°C / -5°C        |  |  |
| Time (t <sub>P</sub> ) within 5°C of 260°C                | 30 seconds               |  |  |
| Ramp-down Rate $(T_P \text{ to } T_L)$                    | 6°C/second max           |  |  |
| Time 25°C to Peak Temperature                             | 8 minutes max.           |  |  |



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